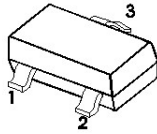


SOT-23

SOT-23 贴片塑封三极管
SOT-23 Plastic-Encapsulate Transistors



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

Marking: CR•

特征 Features

- 与 A733 配对; Complementary to A733
- 最大功率耗散 200mW; Power Dissipation of 200mW
- 高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

- 封装: SOT-23 封装 SOT-23 Small Outline Plastic Package
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter -Base Voltage	V _{EBO}	5	V
Collector Current-Continuous	I _c	150	mA
Collector Power Dissipation	P _c	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	625	°C/W

电特性 (TA = 25°C 除非另有规定)

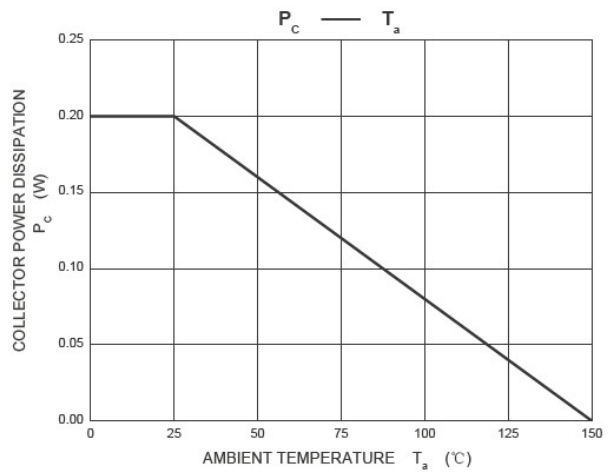
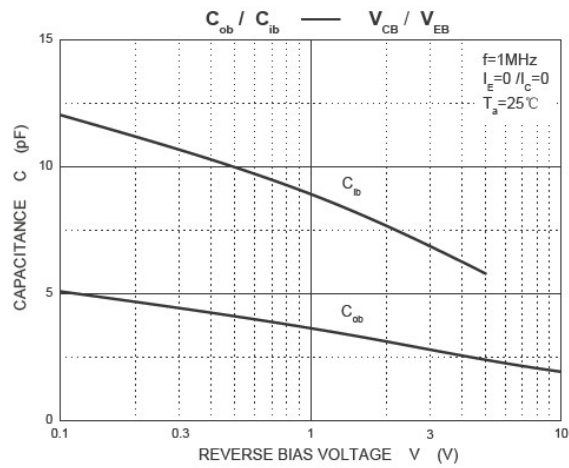
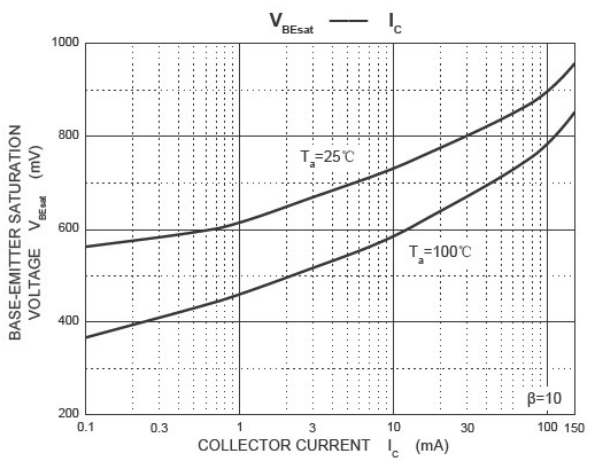
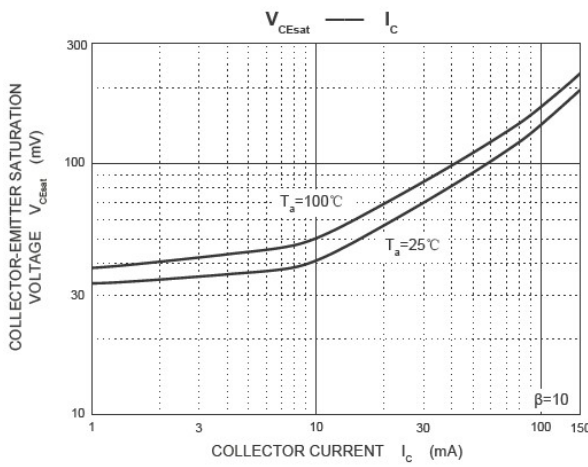
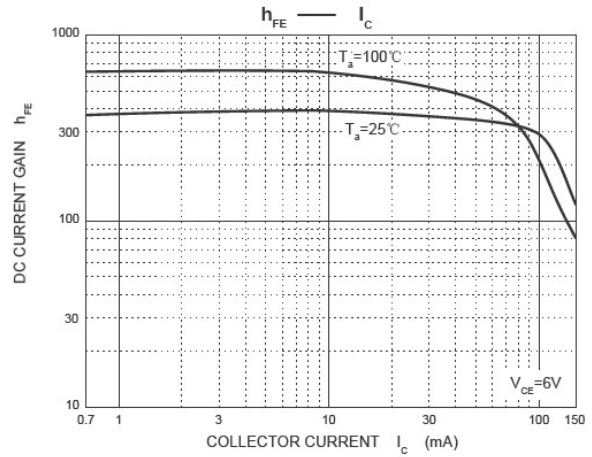
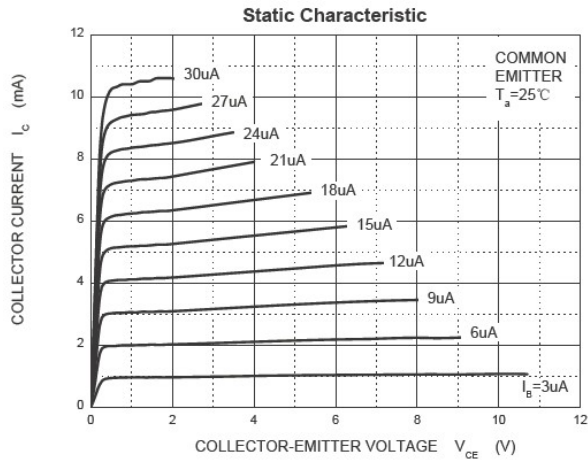
Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits			单位 Unit
			Min	Typ	Max	
Collector-base breakdown voltage	V(BR)CBO	I _C =100uA, I _E =0	60			V
Collector-emitter breakdown voltage	V(BR)CEO	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V(BR)EBO	I _E =100uA, I _C =0	5			V
Collector cut-off current	I _{CER}	V _{CE} =55V, R=100MΩ			100	nA
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			100	nA
DC current gain	h _{FE} (1)	V _{CE} =6V, I _C =1mA	130		400	
	h _{FE} (2)	V _{CE} =6V, I _C =0.1mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA			0.30	V
Base -emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA			1.00	V
Transition frequency	f _t	V _{CE} =6V, I _C =10mA, f=30MHz	150			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			3.0	pF
Noise figure	N _F	V _{CE} =6V, I _C =0.1mA, R _g =10kΩ, f=1KMHz		4	35	dB

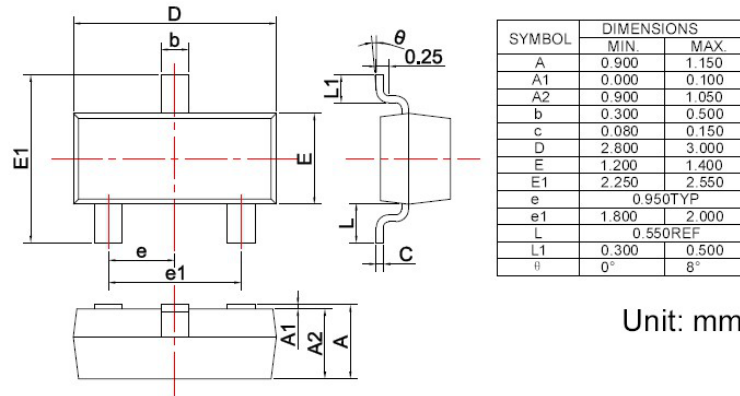
CLASSIFICATION OF h_{FE}(1)

HFE	130-400	
RANK	L	H
RANGE	130-200	200-400

Typical characteristics

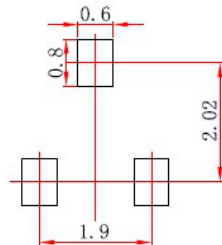


SOT-23 PACKAGE OUTLINE Plastic surface mounted package



焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note:
1. Controlling dimension; in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.

Contact Information

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